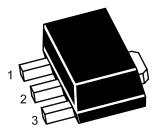
PNP Silicon Expitaxial Planar Power Transistor



1.Base 2.Collector 3.Emitter SOT-89 Plastic Package

Absolute Maximum Ratings (T_a = 25°C)

Parameter	Symbol	Value	Unit
Collector Base Voltage	-Vсво	-Vсво 80	
Collector Emitter Voltage	-V _{CEO}	60	V
Emitter Base Voltage	-V _{EBO} 5		V
Collector Current	-lc	3	А
Peak Pulse Collector Current	-Ісм	6	A
Power Dissipation	PD	1	W
Operating and Storage Temperature Range	Tj ,Tstg	- 55 to + 150	°C

Thermal Characteristics

Parameter	Symbol	Max.	Unit	
Thermal Resistance - Junction to Ambient ¹⁾	Reja	125	°C/W	

¹⁾ Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate in still air.



Characteristics at T_a = 25°C

Parameter	Symbol	Min.	Тур.	Max.	Unit
DC Current Gain at $-I_{C} = 50 \text{ mA}$, $-V_{CE} = 2 \text{ V}$ at $-I_{C} = 500 \text{ mA}$, $-V_{CE} = 2 \text{ V}$ at $-I_{C} = 1 \text{ A}$, $-V_{CE} = 2 \text{ V}$	hfe hfe hfe	70 100 80	- - -	- 300 -	- -
at $-I_{C} = 2 A$, $-V_{CE} = 2 V$	hfe	40	-	-	-
Collector Base Cutoff Current at -V _{CB} = 60 V	-Ісво	-	-	0.1	μA
Collector Base Cutoff Current at -V _{CB} = 60 V, T_A = 100 °C	-I _{CBO}	-	-	10	μA
Emitter Base Cutoff Current at -V _{EB} = 4 V	-I _{EBO}	-	-	0.1	μA
Collector Base Breakdown Voltage at -I _C = 100 μA	-V _{(BR)CBO}	80	-	-	V
Collector Emitter Breakdown Voltage at -I _C = 10 mA	-V _{(BR)CEO}	60	-	-	V
Emitter Base Breakdown Voltage at -I _E = 100 μA	-V _{(BR)EBO}	5	-	-	V
Collector Emitter Saturation Voltage at $-I_c = 1 \text{ A}$, $-I_B = 100 \text{ mA}$	-V _{CE(sat)}	-	-	0.3	V
Collector Emitter Saturation Voltage at $-I_c = 3 A$, $-I_B = 300 mA$	-V _{CE(sat)}			0.6	V
Base Emitter Saturation Voltage at -I _C = 1 A, -I _B = 100 mA	-V _{BE(sat)}	-	-	1.25	V
Base Emitter Turn-On Voltage at -V _{CE} = 2 V, -I _C = 1 A	-VBE(ON)	-	-	1	V
Current Gain Bandwidth Product at $-I_c = 50 \text{ mA}$, $-V_{CE} = 10 \text{ V}$, f = 100 MHz	f⊤	100	-	-	MHz
Turn-On Delay Time at -I _C = 500 mA, -V _{CC} = 10 V,-I _{B1} = -I _{B2} = 50 mA	t _{d(on)}	-	45	-	ns
Turn-Off Delay Time at -I _C = 500 mA, -V _{CC} = 10 V,-I _{B1} = -I _{B2} = 50 mA	t _{off}	-	200	-	ns
Collector Output Capacitance at -V _{CB} = 10 V, f = 1 MHz	Cob	-	-	30	pF



Electrical Characteristics Curves

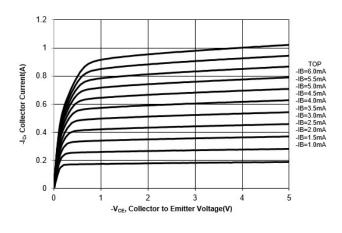


Fig. 1 Output Characteristics Curve

Fig. 2 Collector Current vs. V_{BE}

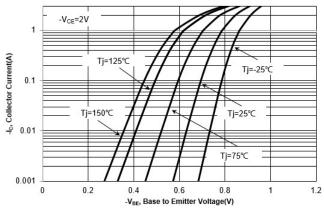
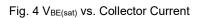
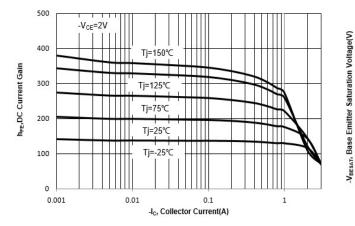
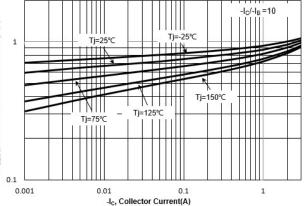


Fig. 3 hFE vs. Collector Current









Electrical Characteristics Curves

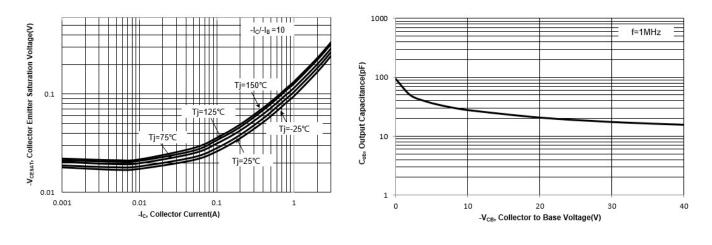
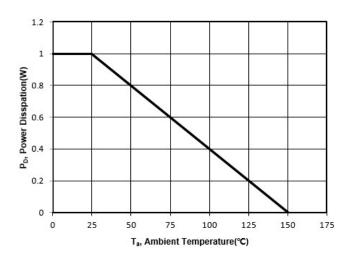


Fig. 5 V_{CE(sat)} vs. Collector Current

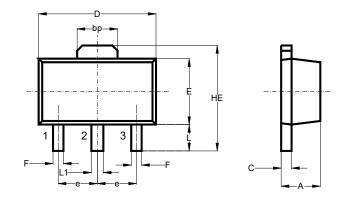
Fig 6. Output Capacitance

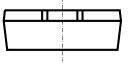
Fig. 7 Power Derating Curve





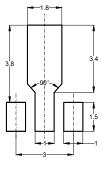
Package Outline (Dimensions in mm)





Unit	А	bp	С	D	E	F	HE	е	L	L1
	1.6	1.60	0.5	4.6	2.6	0.45	4.25	1.5	1.05	0.51
mm	1.4	1.50	0.3	4.4	2.4	0.35	3.75	typ.	0.95	0.41

Recommended Soldering Footprint

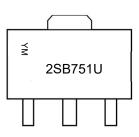


Packing information

	Tape Width	Pitch		Reel Size				
Package	kage (mm) mm		inch	mm	inch	Per Reel Packing Quantity		
0.07.00	40	00.1	0.045 + 0.004	178	7	1,000		
SOT-89	12	8 ± 0.1	0.315 ± 0.004	330	13	4,000		

Marking information

" 2SB751U " = Part No "YM" = Date Code Marking "Y" = Year "M" = Month Font type: Arial



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